

## 2.5 Gbps 850 nm VCSEL

**Part Number: VG2C-7000**

**Applications: 2.125 / 2.5 Gbps**

### Absolute Maximum Ratings (T = 25°C):

| Parameter             | Symbol           | Unit | Min. |  | Max. | Test Condition | Note |
|-----------------------|------------------|------|------|--|------|----------------|------|
| Forward Current       | $I_{\max}$       | mA   |      |  | 15   |                |      |
| Reverse Voltage       | $V_r$            | V    |      |  | 5    |                |      |
| Operating Temperature | $T_{\text{op}}$  | °C   | 0    |  | 85   |                |      |
| Storage Temperature   | $T_{\text{stg}}$ | °C   | - 40 |  | 100  |                |      |
| Maximum Die Exposure  | $T_{\max}$       | °C   |      |  | 260  | For 10 seconds |      |

### Electro-optical Characteristics (T = 25°C, unless noted otherwise):

| Parameter                    | Symbol                 | Unit     | Min. | Typ. | Max. | Test Condition               | Note |
|------------------------------|------------------------|----------|------|------|------|------------------------------|------|
| Threshold Current            | $I_{\text{th}}$        | mA       |      | 2.5  | 3.5  |                              |      |
| Ith Temperature Variation    | $\Delta I_{\text{th}}$ | mA       | -1.5 |      | 1.5  | 25°C to 95°C                 |      |
| Forward Voltage              | $V_f$                  | V        |      | 2.0  | 2.3  | @ 10 mA                      |      |
| Differential Resistance      | $R_s$                  | $\Omega$ |      | 35   | 50   | @ 10 mA                      |      |
| Reverse Voltage              | $V_r$                  | V        | 5    |      |      | @ -10 $\mu$ A                |      |
| Slope Efficiency             | $\eta$                 | mW/mA    | 0.25 | 0.3  | 0.7  | @ 10 mA                      |      |
| Optical Power                | $P_o$                  | mW       | 1.5  | 2.6  |      | @ 10 mA                      |      |
| Slope Efficiency temp-coeff. | $\Delta\eta/\Delta T$  | %/°C     | -0.6 |      |      | 25-90°C<br>@ 10 mA           |      |
| Peak Wavelength              | $\lambda$              | nm       | 830  | 845  | 860  | @ 2 mW                       |      |
| Beam Divergence              | $\theta$               | deg      |      |      | 30   | Full width, 1/e <sup>2</sup> |      |
| Rise Time                    | $\tau_r$               | ps       |      | 90   |      | 20-80%                       |      |
| Fall Time                    | $\tau_f$               | ps       |      | 100  |      | 20-80%                       |      |

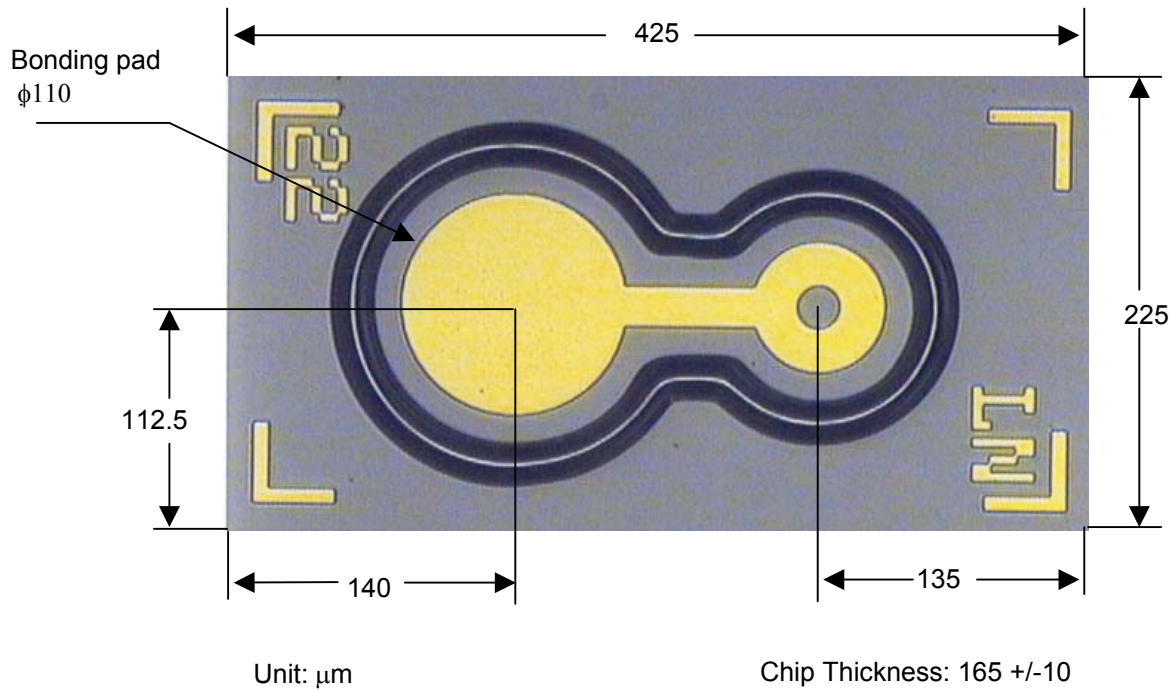
Chip configuration:

1. Top contact: Anode; Bottom contact: Cathode.
2. Dimension: 225  $\mu$ m (Wide) x 425  $\mu$ m (Long) x 165  $\mu$ m (Thick)

\* Specifications are subject to change without notice.

\* Screening per customer-specified reject limits is available.

May, 2002



VCSEL Chip Top View